SILICON (Si) POWER MOSFET ▲ CET6362



CET MOS

CET6362

60V ▲ 38mΩ ▲ 6.4A ▲ Si MOSFET

SILICON Si MOSFET ▲ SMD type N-channel enhancement mode UL94V-0 rated flame retardant epoxy SOT223 package ▲ MSL 3 Super high dense cell density for extremely low R_{DS(ON)} Rugged and reliable

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RoHS

REACH

MAXIMUM RATINGS

Parameter ($T_A = 25^{\circ}C$, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	60V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current	I _D	6.4A
Pulsed Drain Current Note 1	I _{DM}	16A
Maximum Power Dissipation	PD	3W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

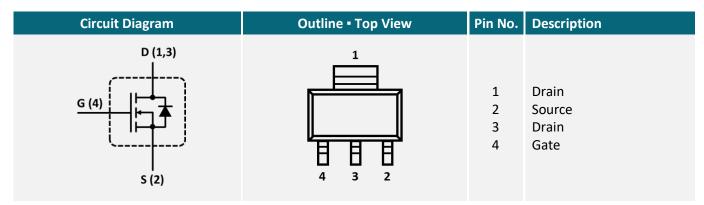
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	42°C/W

APPLICATIONS

Battery Management	DC/DC	DC	Industrial	Power
Systems	Converter	Fan	Control	Switches
+ 4 -				

PIN DESCRIPTION



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ELECTRICAL CHARACTERISTICS A T_A = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$	BV _{DSS}	60			V
Zero Gate Voltage Drain Current	$V_{DS} = 60V, V_{GS} = 0V$	I _{DSS}			1	μA
Gate Body Leakage Current, Forward	$V_{GS} = 20V, V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	V_{GS} = -20V, V_{DS} = 0V	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250 \mu A$	V _{GS(th)}	1		2.5	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_{D} = 5A$	R _{DS(ON)}		38	46	mΩ
Static Drain-Source On-Resistance	V_{GS} = 4.5V, I_{D} = 4A	R _{DS(ON)}		41	53	mΩ
Dynamic Characteristics Note 4						
Input Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{ISS}		750		рF
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$	Coss		65		рF
Reverse Transfer Capacitance	V_{DS} = 25V, V_{GS} = 0V, f = 1MHz	C _{RSS}		50		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = 30V, V_{GS} = 10V, I_D = 1A, $R_{G(ext)}$ = 6 Ω	t _{D(ON)}		11		ns
Turn-On Rise Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 1A, $R_{G(\text{ext})}$ = 6Ω	t _R		4		ns
Turn-Off Delay Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 1A, $R_{G(\text{ext})}$ = 6Ω	t _{D(OFF)}		51		ns
Turn-Off Fall Time	V_{DD} = 30V, V_{GS} = 10V, I_{D} = 1A, $R_{G(\text{ext})}$ = 6Ω	t _F		7		ns
Total Gate Charge	V_{DS} = 30V, V_{GS} = 4.5V, I_D = 4.5A	Q_{G}		9.7		nC
Gate Source Charge	V_{DS} = 30V, V_{GS} = 4.5V, I_D = 4.5A	Q _{GS}		1.6		nC
Gate Drain Charge	V_{DS} = 30V, V_{GS} = 4.5V, I_{D} = 4.5A	\mathbf{Q}_{GD}		4.2		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current ^{Note 3}		۱ _s			2.3	А
Drain-Source Diode Forward Voltage ^{Note 3}	$V_{GS} = 0V$, $I_S = 1A$	V_{SD}			1.3	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board, t \leq 10 sec

3: Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

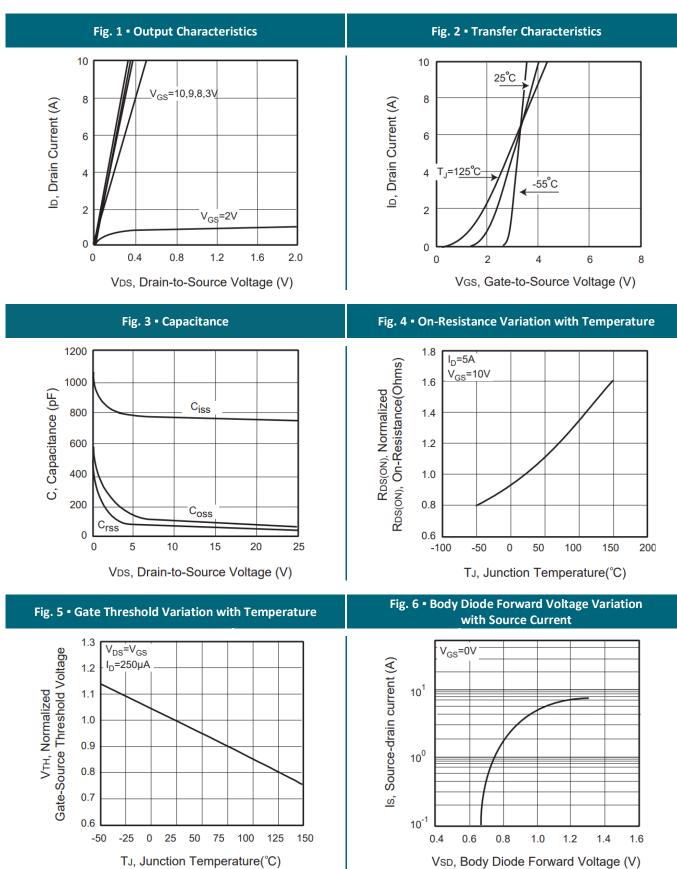
4: Guaranteed by design, not subject to production testing.



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REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



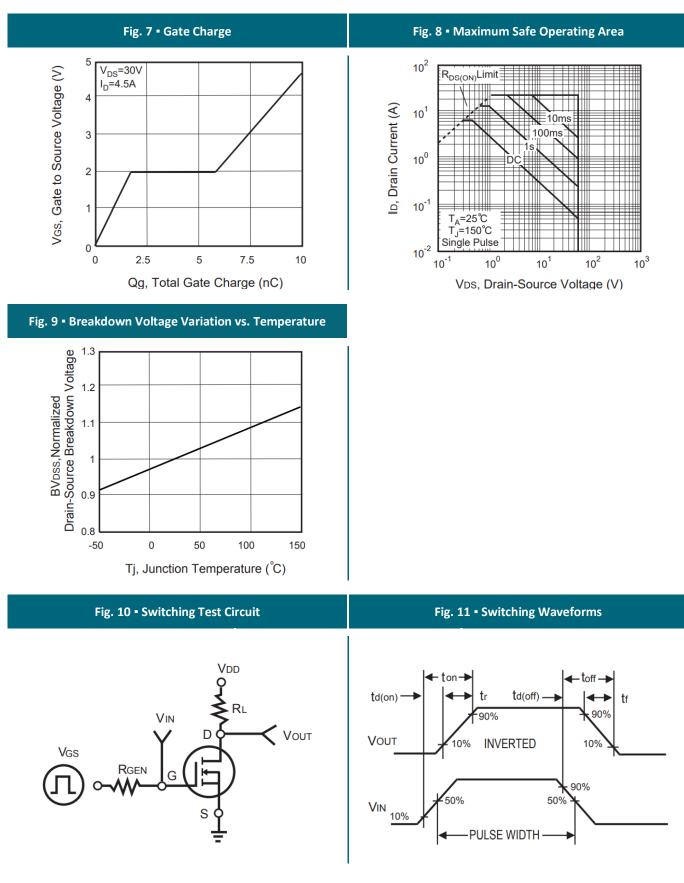
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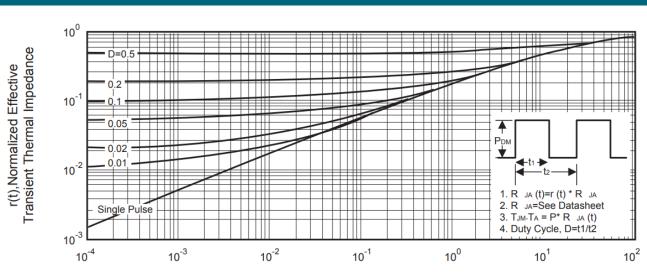
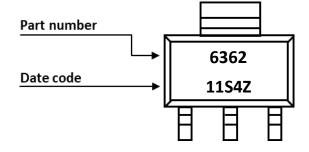


Fig. 12 • Normalized Thermal Transient Impedance Curve

Square Wave Pulse Duration (sec)

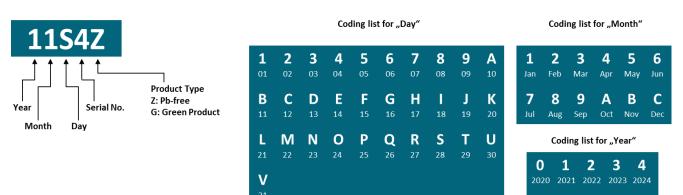
PART MARKING



DATE CODE

Example: 11S4Z

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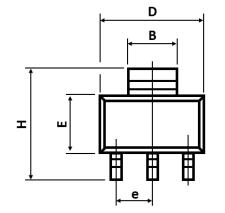
7 2025 2026 2027 2028 2029

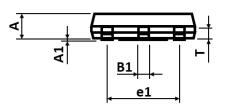
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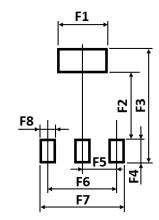


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PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT







Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	S
А	1.500	-	1.700	(
A1	0.020	-	0.100	
В	2.950	-	3.200	
B1	0.670	-	0.800	
С	0.240	-	0.350	
D	6.300	-	6.850	
е		2.300 TYP		

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
e1		4.600 TYP	
E	3.300	-	3.800
н	6.700	-	7.300
L	0.900	-	-
Т	0.600	-	0.800
θ		10° MAX	

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	3.500	-	F5	-	2.300	-
F2	-	4.600	-	F6	-	4.600	-
F3	-	8.000		F7	-	5.600	-
F4	-	1.600		F8	-	1.200	-

θ

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

2. For further information, please reference document IPC-7351A.

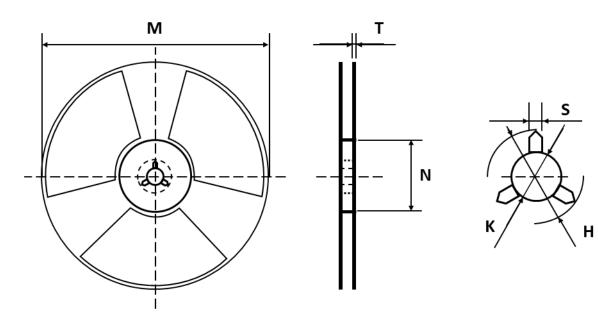
ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.	
CET6362	SOT223	7" Reel	2,500pcs	5,000pcs	15,000pcs	



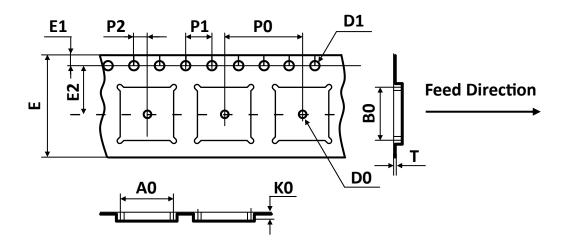


REEL DIMENSIONS All dimensions in mm



Tape Size	Reel Size	М	Ν	т	н	К	S
8mm	Ø180	Ø178.00	Ø54.00	1.20	20.00	13.30	3.00
011111	Ø100	±1.00	±0.50	±0.20	±1.00	±0.30	±1.00

TAPE DIMENSIONS All dimensions in mm



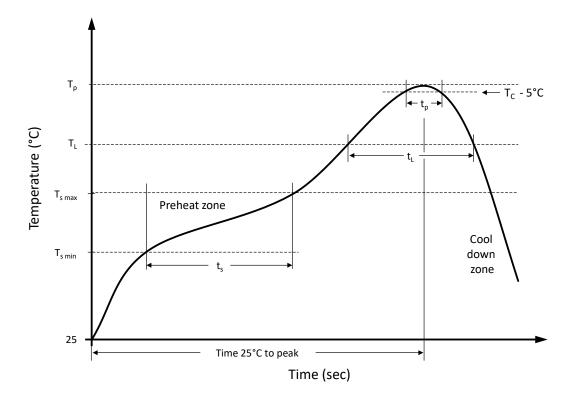
Ра	ckage	A0	B0	К0	D0	D1	E	E1	E2	P0	P1	P2	Т
60	DT223	2.40	2.60	1.20	1.00	1.50	8.00	1.75	3.50	4.00	4.00	2.00	0.20
SC	51225	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.





RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features	Profile Features		Pb-Free Assembly
Preheat temperature min.	T_{smin}	100 °C	150 °C
Preheat temperature max.	T_{smax}	150 °C	200 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	120 seconds	120 seconds
Ramp-up rate (T _L to T _p)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	ΤL	183 °C	217 °C
Time t_L maintained above T_L	tL	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	tp	20 seconds max.	30 seconds max.
Ramp-down rate (T_L to T_p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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